

isc N-Channel MOSFET Transistor

2SK2389

DESCRIPTION

- Drain Current I_D= 5A@ T_C=25 °C
- · Drain Source Voltage-
 - : V_{DSS}= 700V(Min)
- · Fast Switching Speed
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

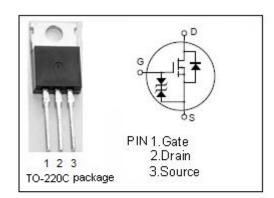
APPLICATIONS

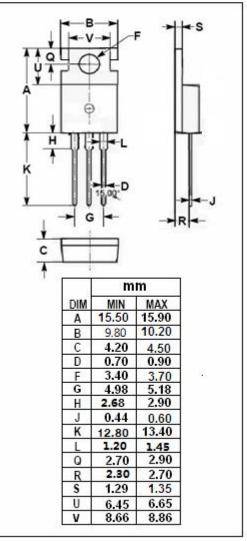
Switching regulators



ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL	ARAMETER	VALUE	UNIT
V_{DSS}	Drain-Source Voltage (V _{GS} =0)	700	V
V_{GS}	Gate-Source Voltage	±30	V
I _D	Drain Current-continuous@ TC=25℃	5	Α
P _{tot}	Total Dissipation@T _C =25℃	125	W
Tj	Max. Operating Junction Temperature	150	$^{\circ}$
T _{stg}	Storage Temperature Range	-55~150	$^{\circ}$







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• ELECTRICAL CHARACTERISTICS (T_C=25°C)

SYMBOL	PARAMETER	CONDITIONS	MIN	TYPE	MAX	UNIT
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0; I _D = 1mA	700			V
V _{GS} (th)	Gate Threshold Voltage	V _{DS} = V _{GS} ; I _D =1mA	1.5		3.5	V
R _{DS(on)}	Drain-Source On-Resistance	V _{GS} = 10V; I _D = 2.0A			1.7	Ω
I _{GSS}	Gate-Body Leakage Current	V _{GS} = ±30V;V _{DS} = 0			±100	nA
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =700V; V _{GS} = 0			500	μΑ



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